



Time: 3 hrs.

Max. Marks: 100

Sixth Semester B.E. Degree Examination, June/July 2016

Microelectronic Circuits

Note: Answer FIVE full questions, selecting any Three from Part-A and Two from Part-B.

PART - A

1. a. Derive the expression of $i_D - V_{DS}$ relationship for triode and saturation region of a NMOS transistor. (10 Marks)
- b. For the MOSFET with $\frac{W}{L} = \frac{8 \mu\text{m}}{0.8 \mu\text{m}}$, calculate the values of V_{GS} and $V_{DS(\min)}$ needed to operate the transistor in the saturation region with a dc current $I_D = 100$. Assume $K'_n = 194 \mu\text{A/V}^2$ and $V_t = 0.7 \text{ V}$. (05 Marks)
- c. Write the expression for the relationship between V_{SB} and V_t . Mention the effect of V_{SB} on the channel. (05 Marks)

2. a. What are the benefits of short channel MOSFETs? (06 Marks)
- b. Explain the operation of a MOSFET current mirror. (06 Marks)
- c. Draw the circuit of a MOS current steering circuit and explain it. (08 Marks)

3. a. Explain CMOS implementation of the common source amplifier and also draw its i-v characteristic of the active load and transfer characteristic. (10 Marks)
- b. Consider a common gate amplifier specified as follows :

$$\frac{W}{L} = \frac{7.2 \mu\text{m}}{0.36 \mu\text{m}}, \mu_n C_{OX} = 387 \mu\text{A/V}^2, \gamma_0 = 18 \text{ K}\Omega, I_D = 100 \mu\text{A}, g_m = 1.25 \text{ mA/V}, \chi = 0.2,$$
 $R_S = 10 \text{ K}\Omega, R_L = 100 \text{ K}\Omega, C_{gs} = 20 \text{ fF}, C_{gd} = 5 \text{ fF}$ and $C_L = 0$. Find A_{VO} , R_{in} , R_{out} , G_V , G_{is} , G_i and f_H . (10 Marks)

4. a. What is cascade amplifier? Mention the basic idea behind it. (04 Marks)
- b. Derive the expression of voltage gain and open circuit voltage gain of a IC-source follower. Draw its small signal equivalent circuit model. (08 Marks)
- c. Explain the operation of a MOS differential pair with common-mode input voltage. (08 Marks)

5. a. Explain the operation of a two-stage CMOS op-amp configuration. Mention its features. (10 Marks)
- b. Illustrate the method of differential to single-ended conversion. (07 Marks)
- c. What are the factors contribute to the dc offset voltage of the MOS differential pair? (03 Marks)

PART - B

6. a. Discuss the properties of negative feedback in details. (08 Marks)
- b. Explain the relationship between stability and pole location of an amplifier with effects. (06 Marks)
- c. Draw the block diagram, representation of a series-shunt feedback amplifier and derive the expression of input resistance with feedback. (06 Marks)

7. a. Design a non-inverting amplifier with a gain of 2. At the maximum output voltage of 10 V and the current in the voltage divider is to be $10 \mu\text{A}$. (05 Marks)
- b. With a mathematical analysis and circuits, explain the temperature effects in Logarithmic amplifier are to be minimized. (09 Marks)
- c. Draw the sample and hold circuit using op-amp and explain it. (06 Marks)
8. a. Define the following parameters of a logic circuit family and write the expressions : (08 Marks)
- i) Propagation delay.
 - ii) Robustness
 - iii) Delay-power product.
 - iv) Dynamic power dissipation.
 - b. Implement : (12 Marks)
- i) $F = AB + CD$ using the AND-OR-INVERT gate logic.
 - ii) $F = (A + B)(C + D)$ using the OR-AND-INVERT gate logic.
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